

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Makoto IIDA, Masanori KIMURA

Application No.: U. S. National Stage of  
PCT/JP00/07809

Filed: July 9, 2001

Docket No.: 110051

For: SILICON SINGLE CRYSTAL WAFER, METHOD FOR PRODUCING THE SAME  
AND SOI WATER

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 1-12 without prejudice to or disclaimer of the subject matter  
contained therein.

Please add new claims 13-33 as follows:

W, Sub B  
--13. A silicon single crystal wafer grown by the Czochralski method, which is  
doped with nitrogen, and has an N-region for the entire plane and an interstitial oxygen  
concentration of 8 ppma or less.--

--14. A silicon single crystal wafer grown by the Czochralski method, which is  
doped with nitrogen, and has an interstitial oxygen concentration of 8 ppma or less, and in  
which at least void type defects and dislocation clusters are eliminated from the entire plane.--